

PROGRAM
ISPlasma2010
2nd International Symposium on Advanced Plasma Science and
its Applications for Nitrides and Nanomaterials

MAR 7 (Sun)	MAR 8 (Mon)			MAR 9 (Tue)			MAR 10 (Wed)									
	Registration (9:00-9:20)			Registration (9:00-9:20)			Registration (9:00-9:20)									
Opening/Plenary Lecture <ROOM A>	(9:20-9:35) Opening	Plasma 3. Etching Process I <ROOM A>	(9:20-9:50) Keynote Lecture 9a-A01KA M. Goeckner (University of Texas at Dallas, USA) "Plasma-Surface Interactions-temperature Affects"	Nitride 3. RF-MBE I <ROOM B>	(9:20-9:50) Keynote Lecture 9a-B01KB Y. Cordier (CRHEA-CNRS, FRANCE) "Comparison of GaN Based Structures Grown by Molecular Beam Epitaxy Using Nitrogen Plasma and"	Nanocarbons 3. Solar Cells Based on Organic Materials <ROOM C>	(9:20-9:50) Keynote Lecture 9a-C01KC S. Fukuzumi (Osaka University) "Nanomaterials for Artificial Photosynthesis"	Plasma 5. CVD Process <ROOM A>	(9:20-9:50) Keynote Lecture 10a-A01KA R. d'Agostino (University of Bari, ITALY) "Plasma Nanostructured Fluoro-Polymers"	Nitride 7. White LEDs <ROOM B>	(9:20-9:50) Keynote Lecture 10a-B01KB K. Ota (TOYODA GOSEI Co., Ltd.) "History of GaN LED and its Progress"	Nanomaterials 5. Composite/Functionally Graded Materials <ROOM C>	(9:20-9:50) Keynote Lecture 10a-C01KC L. A. Rocha (University of Minho, PORTUGAL) "Functionalization of Ti Surfaces for Biomedical Applications"			
	(9:35-9:45) Project Director (Aichi Science & Technology Foundation) "Tokai Region Nanotechnology Manufacturing Cluster and its Expansion Program"		(9:50-10:10) 9a-A02OA S. Barnola (GEA-LETTI-MINATEC) "Challenges in Plasma Etching of Narrow 3D Gate All Around Devices"		(9:50-10:10) 9a-B02OB T. Ohachi (Doshisha University) "RF Nitrogen Source for MBE Growth of Group III Nitrides on Si and its Application for AM-MEE"		(9:50-10:10) Invited Lecture 9a-C02IC T. Yoshida (Gifu University) "Electrochemical Self-Assembly of Nanostructured ZnO/Dye Hybrid Thin Films for Solar Cells"		(9:50-10:10) Keynote Lecture 10a-A02KA U. R. Kortshagen (University of Minnesota, USA) "Plasma Synthesis of Silicon Inks and their Applications for Renewable Energy Solutions"		(9:50-10:10) Invited Lecture 10a-B02IB V. Haerle (OSRAM, GERMANY) Title to be assigned.		(9:50-10:10) 10a-C02OC E. Miura-Fujiwara (Nagoya Institute of Technology) "Fabrication of Metal-based Functionally Graded Grinding Wheel Dispersing Fine Ceramic Particles by a Centrifugal Mixed-powder Method"			
	(9:45-10:15) Plenary Lecture 8a-A01S S. Iijima (Meijo University) "Structure Characterization of Nano-carbon Materials on the Atomic Resolution Basis"		(10:10-10:30) 9a-A03OA S.-W. Cho (Korea AJOU University) "Effect of CH2F2 Addition on the Angular Dependence of Si3N4 Etch Rates and SiO2-to-Si3N4 Etch Selectivity in a C4F8/Ar/O2 Plasma"		(10:10-10:30) 9a-B03OB S. Chen (Nagoya University) "Radical Kinetics in N2-H2 Plasma Generated by Novel High Density Radical Source"		(10:10-10:30) 9a-C03OC S. Adhikari (Chubu University) "Both Single Walled and Multi Walled Carbon Nanotubes Incorporated Organic Solar Cells"		(10:10-10:30) Invited Lecture 10a-A03IA T. Yoshida (The University of Tokyo)		(10:10-10:30) 10a-B03OB C.-C. Kao (National Cheng Kung University) "Localized Surface Plasmon-Enhanced GaN-based Light-Emitting-Diode with Ag Nanotriangles Array by Nanosphere Lithography"		(10:10-10:30) 10a-C03OC M. Tokita (Bits Company Limited) "Development of Industrial Products on Functionally Graded Materials by Spark Plasma Sintering (SPS) Method"			
(10:15-10:35) Coffee Break			(10:30-10:50) Coffee Break			(10:40-10:50) Coffee Break			(10:30-10:50) Coffee Break							
Knowledge Cluster Initiative (The Second Stage)-Tokai Region Nanotechnology Manufacturing Cluster <ROOM A>	(10:35-11:00) Knowledge Cluster Lecture 8a-A02C M. Hori (Nagoya University) "Fundamental Research on Plasma Nanoprocessing"	Plasma 4. Etching Process II <ROOM A>	(10:50-11:20) Keynote Lecture 9a-B04KB J. P. Chang (UC Los Angeles, USA) "Multifunctional Oxide Materials: Synthesis and Patterning"	Nitride 4. RF-MBE II <ROOM B>	(10:50-11:20) Keynote Lecture 9a-B04KB B. Daudin (CEA Grenoble, FRANCE) "Growth, STRUCTURAL and Optical Properties of GaN/AlN Nanowire Heterostructures"	Nanomaterials 4. Surface Modification/Surface Functionalization <ROOM C>	(10:50-11:20) Keynote Lecture 9a-C04KC J. Patscheider (EMPA, SWITZERLAND) "Hard and Optically Transparent Al-Si-N Thin Films: Solid Solutions, Nanocomposites and Nanomultilayers"	Plasma 6. Solar Cells Based on Plasma Science <ROOM A>	(10:50-11:20) Keynote Lecture 10a-A04KA T. Takamoto (SHARP CORPORATION) "High Efficiency III-V Multijunction Solar Cells"	Nitride 8. UV Devices <ROOM B>	(10:50-11:20) Keynote Lecture 10a-B04KB C. J. Sun (ITRI, TAIWAN) "UV WLED for Wide Color Gamut Display Application"	Nanomaterials 6. Nanoparticles <ROOM C>	(10:50-11:20) Keynote Lecture 10a-C04KC P. Milani (The University of Milan, ITALY) "Pulsed Microplasma Cluster Source: A Powerful Tool for the Integration of Nanomaterials on Microdevices"			
	(11:00-11:15) Knowledge Cluster Lecture 8a-A03C H. Amano (Meijo University) "Comparative Study on the Growth of Group III Nitrides by Plasma-MBE and MOVPE"		(11:20-11:40) 9a-A05OA T. Kachi (Toyota Central R&D Labs., Inc.) "Suppression of Leakage Current through the pn Junction Fabricated on Etched Surfaces of GaN"		(11:20-11:40) 9a-B05OB H. Umeda (Ritsumeikan University) "Fabrication of InN/InGa Multi Quantum Well Structures by Droplet Elimination by Radical-beam Irradiation"		(11:20-11:40) Invited Lecture 9a-C05IC M. Kogoma (Sophia University) "Surface Treatment of Fine Powders Using Atmospheric Pressure Glow Discharge"		(11:20-11:40) 10a-A05OA M. Umeno (Chubu University) "Synthesis of Carbon Thin Film for Solar Cells Application"		(11:20-11:40) 10a-B05OB Y. Sakai (Nagoya Institute of Technology) "MOCVD Growth and Characterization of AlInN-based Schottky Ultraviolet Photodiodes on AlN Template"		(11:20-11:40) 10a-C05OC K. Sumiyama (Nagoya Institute of Technology) "Fe-Si Core/Si Shell Clusters Prepared by Collisions of Fe and Si Clusters in a Plasma-Gas-Condensation System"			
	(11:15-11:30) Knowledge Cluster Lecture 8a-A04C T. Egawa (Nagoya Institute of Technology) "Growth and Device Application of GaN on Si"		(11:40-12:00) 9a-A06OA C. S. Moon (Nagoya University) "A Well-Established Compact Combinatorial Etching Process Employing Inductively Coupled H2/N2 Plasma"		(11:40-12:00) 9a-B06OB J. L. Guyaux (RIBER SA) "Current and Future's Development of Thinfilm Technology"		(11:40-12:00) 9a-C06OC J. Musil (University of West Bohemia) "Hard Nanocomposite Coatings: Mechanical and Tribological Properties, Thermal Stability and Protection against Oxidation above 1000 °C"		(11:40-12:00) 10a-A06OA Y. Kawashima (Kyushu University) "Synthesis of Crystalline Si Nanoparticles for Quantum Dots Sensitized Solar Cells"		(11:40-12:00) 10a-B06OB F. Matsuno (Toyoashi University of Technology) "Intelligent UV Sensor Composed of GaN-based Photodiode and Si-charge Transfer Type Signal Processor"		(11:40-12:00) 10a-C06OC H. Miyata (Kyusyu University) "Control of Surface Roughness of Nano-particle Composite Lowk Film Deposited in CVD Plasma"			
	(11:30-11:45) Knowledge Cluster Lecture 8a-A05C O. Takai (Nagoya University) "Progress in Solution Plasma Processing"		(12:00-13:00) Lunch				(12:00-13:00) Lunch				(12:00-13:00) Lunch					
	(11:45-12:00) Knowledge Cluster Lecture 8a-A06C Y. Watanabe (Nagoya Institute of Technology) "Development of Nanocomposites Based on Interface Engineering"		(13:00-14:30) Poster Session A				(13:00-14:30) Poster Session B				(13:00-14:30) Poster Session B					
Plasma 1. Advanced Plasma Measuring Technology <ROOM A>	(14:30-15:00) Keynote Lecture 8p-A01KA U. Czarnetzki (Ruhr University, Bochum, GERMANY) "The Optical Probe: A Novel Device for Spatially Resolved Optical Emission Spectroscopy in Plasmas"	Nitride 1. Nitride Electronic Devices <ROOM B>	(14:30-15:00) Keynote Lecture 8p-B01IB S. Arulkumaran (Nanyang Technological University, SINGAPORE) "High Performance AlGaIn/AlN/ GaN High-Electron-Mobility Transistors on Silicon"	Nanomaterials 1. Nanocarbon Materials I <ROOM C>	(14:30-15:00) Keynote Lecture 8p-C01KC J. Robertson (Cambridge University, UK) "Plasma Deposition of Diamond-like Carbon Films"	Nitride 5. Advanced Nitride Devices <ROOM A>	(14:30-15:00) Keynote Lecture 9p-A01KB S. Noda (Kyoto University) "Photonic Crystals and Their Application to GaN System"	Plasma 7. Advanced Plasma Applications and Industry-Academia-Government Collaboration <ROOM A>	(14:30-15:00) Keynote Lecture 10p-A01KA T. Higashi (Tokyo Electron Limited) "Global Competitive Strength by Core Technology"	Simultaneous Interpretation						
	(15:00-15:20) Invited Lecture 8p-B02IB K. Urabe (Kyoto University) "Spatial Distribution of Electron Density in a Parallel-plate Dielectric Barrier Discharge Measured by CO2-laser Heterodyne Interferometry"		(15:00-15:20) Topical Lecture 8p-C02TC H. Ohara (Nippon ITF Inc.) "Industrial Applications of DLC and their Scientific Aspects"		(15:00-15:30) Keynote Lecture 9p-A02KB N. Grandjean (EPFL, SWITZERLAND)		(15:00-15:30) Keynote Lecture 10p-A02KA J. G. Han (CAPST, Sungkyunkwan University, KOREA) "Synthesis of Functional Hybrid Films on Polymer by Dual RF Plasma CVD"		Simultaneous Interpretation							
	(15:20-15:40) 8p-A03OA C. Koshimizu (TOKYO ELECTRON AT LTD.) "Temperature Measurement of Silicon Wafer in Plasma Etching Process Using Low-coherence Interferometry"		(15:10-15:30) 8p-B03OB T. Fukuda (Tohoku University) "Prospects for the Acidic Ammonothermal Growth of GaN Crystal"		(15:20-15:40) Topical Lecture 8p-C03TC M. Hasegawa (National Institute of Advanced Industrial Science and Technology) "Low Temperature Nano-crystalline Diamond Film Synthesis using Surface Wave Plasma Chemical Vapor"		(15:30-16:00) Keynote Lecture 9p-A03KB U. K. Mishra (UC Santa Barbara, USA) "The Use of Plasma in the Growth and the Processing of Gallium Nitride Materials"		(15:30-16:00) Keynote Lecture 10p-A03KA E. Schultheiss (Fraunhofer Institute, GERMANY) "Technology Transfer in Germany; the Fraunhofer Model"		Simultaneous Interpretation					
	(15:40-16:00) 8p-A04OA Q. Zhang (Chubu University) "Plasma Electron Monitoring with Multi-Resonator Frequency Shift Probe"		(15:30-15:50) 8p-B04OB S. L. Selvaraj (Nagoya Institute of Technology) "Improved Breakdown by Suppressing Gate Leakage Using 2nm i-GaN Cap layered AlGaIn/GaN HEMTs on Silicon"		(15:40-16:00) Topical Lecture 8p-C04TC H. Yamada (AIST) "A Description of Reactive Microwave-plasma-CVD of Single-crystal-diamond"		(16:00-16:20) Invited Lecture 9p-A04IB T. Uesugi (Toyota Central R&D Labs., Inc.) "GaN Power Switching Devices for Automotive Applications"		(16:00-16:30) Keynote Lecture 10p-A04KA W. Izumiya (Sangyo Times, Inc.) "Environment and Energy is the Second Industrial Revolution!"		Simultaneous Interpretation					
(16:00-16:20) Coffee Break			(16:00-16:20) Coffee Break			(16:20-16:40) Coffee Break			(16:30-16:50) Coffee Break							
Plasma 2. Simulation <ROOM A>	(16:20-16:50) Keynote Lecture 8p-A05KA M. J. Kushner (University of Michigan, USA) "Customizing Plasma Sources for Advanced Materials Synthesis"	Nitride 2. Growth of GaN and Related Materials <ROOM B>	(16:20-16:50) Keynote Lecture 8p-B05KB T. Fukuda (Tohoku University) "Prospects for the Acidic Ammonothermal Growth of GaN Crystal"	Nanomaterials 2. Nanocarbon Materials II <ROOM C>	(16:20-16:50) Keynote Lecture 8p-C05KC Y. Wu (National University of Singapore, SINGAPORE) "Growth of Two-dimensional Carbon Nanostructures and their Electrical Transport Properties"	Nitride 6. Application of Advanced Plasma Technology for Nitride Semiconductors <ROOM A>	Plasma 8. Application Front of Advanced Plasma Science and Industry-Academia-Government Collaboration <ROOM A>	Simultaneous Interpretation								
	(16:50-17:10) 8p-A06OA A. Ito (National Institute for Fusion Science) "Molecular Dynamics Simulation of Chemical Sputtering and Chemical Vapor Deposition on Carbon Materials"		(16:50-17:10) 8p-B06OB H. Y. Geng (FURUKAWA CO., LTD.) "Residual Strain Evaluation by Cross-sectional Micro-reflectance Spectroscopy of Freestanding GaN Grown by HVPE"		(16:50-17:10) Invited Lecture 8p-C06IC T. Nozaki (Tokyo Institute of Technology) "A Pressure-induced Transition of Carbon Nanotube Morphology in Plasma Enhanced CVD"				(16:40-18:10) Panel Discussion ~Application of Advanced Plasma Technology for Nitride Semiconductors~ (Moderator) Y. Nanishi (Ritsumeikan University) (Panelists) H. Amano (Meijo University) B. Daudin (CEA Grenoble, FRANCE) N. Grandjean (EPFL, SWITZERLAND) T. Hashizume (Hokkaido University) H. Kano (NU Eco Engineering Co., LTD.) U. K. Mishra (UC Santa Barbara, USA) T. Okumura (Tokyo Metropolitan University)	(16:50-18:20) Panel Discussion ~Application Front of Advanced Plasma Science and Industry-Academia-Government Collaboration~ (Moderator) W. Izumiya (Sangyo Times, Inc.) (Panelists) M. Goeckner (University of Texas at Dallas, USA) J. G. Han (CAPST, Sungkyunkwan University, KOREA) M. Hori (Nagoya University) S. Hosaka (Tokyo Electron Limited) M. Sato (MARUBUN CORPORATION) E. Schultheiss (Fraunhofer Institute, GERMANY)						
(17:00-18:00) Registration	(17:10-17:30) 8p-A07OA H. Kousaka (Nagoya University) "Numerical Simulation of High-density Plasma Column Sustained in Narrow Metal Tube with Microwave Propagation along Plasma-sheath Interface"	(17:10-17:30) 8p-B07OB D. Iida (Meijo University) "Growth of GaInN Films by Raised Pressure MOVPE System at 200kPa"	(17:10-17:30) 8p-C07OC S. C. Chen (National Cheng Kung University) "Magneto-optical Properties of Armchair Nanographene Ribbons Under the Modulated Electric Field"	(18:10-19:40) Banquet (Cafeteria in Meijo University)			(18:20-18:30) Closing			(18:30-19:30) Display Carry-out						
(18:00-19:30) Welcome Party (Student Hall in Meijo University)	(17:30-19:00) Poster Session A			(18:10-19:40) Banquet (Cafeteria in Meijo University)			(18:20-18:30) Closing			(18:30-19:30) Display Carry-out						